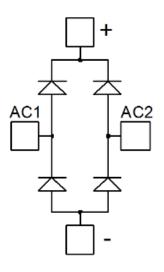
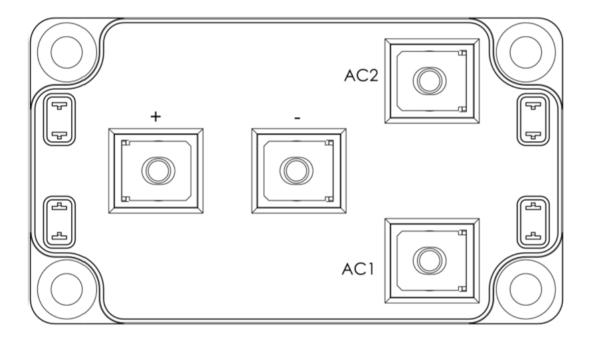


MSCDC200H70AG SiC Diode Full Bridge Power Module

1 Product Overview

This section provides the product overview for the MSCDC200H70AG device.





All ratings at $T_j = 25$ °C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.



1.1 Features

The following are key features of the MSCDC200H70AG device:

- Silicon carbide (SiC) Schottky diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature-independent switching behavior
 - Positive temperature coefficient on VF
- High blocking voltage
- Low stray inductance
- M5 power connectors
- Aluminum nitride (AIN) substrate for improved thermal performance

1.2 Benefits

The following are benefits of the MSCDC200H70AG device:

- Outstanding performance at high-frequency operation
- Low losses
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

1.3 Applications

The MSCDC200H70AG device is designed for the following applications:

- Uninterruptible power supply (UPS)
- Induction heating
- Welding equipment
- High-speed rectifiers



2 Electrical Specifications

This section provides the electrical specifications for the MSCDC200H70AG device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per diode for the MSCDC200H70AG device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
Vrrm	Repetitive peak reverse voltage		700	V
lf	DC forward current	Tc = 65 °C	200	А

The following table shows the thermal and package characteristics of the MSCDC200H70AG.

Table 2 • Thermal and Package Characteristics

Symbol	Characteristic			Min	Max	Unit
VISOL	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz			4000		V
TJ	Operating junction temperature range			-40	175	°C
Τιορ	Recommended junction temperature under switching conditions			-40	T _{Jmax} -25	
Tstg	Storage temperature range			-40	125	
Tc	Operating case temperature			-40	125	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package weight				300	g

2.2 Electrical Performance

The following table shows the electrical characteristics per diode of the MSCDC200H70AG.

Symbol	Characteristic Diode forward voltage	Test Conditions		Min	Тур	Max	Unit
VF		IF = 200 A	T _j = 25 °C		1.5	1.8	V
			Tj = 175 °C		1.9		
Irm	Reverse leakage current	V _R = 700 V	T _j = 25 °C		60	800	μA
			Tj = 175 °C		1000		
Qc	Total capacitive charge	$V_R = 400 V$			532		nC
С	Total capacitance	f = 1 MHz, V _R :		992		pF	
		f = 1 MHz, V _R :	= 400 V		864		
RthJC	Junction-to-case thermal resistance					0.241	°C/W

Table 3 • Electrical Characteristics Per Diode



2.3 Performance Curves

This section shows the typical performance curves for the MSCDC200H70AG device.

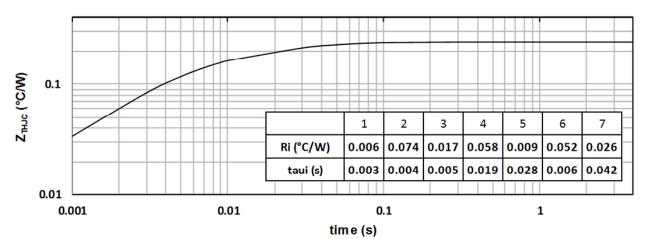
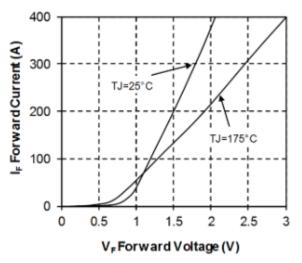
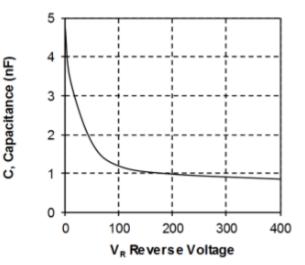


Figure 1 • Maximum Transient Thermal Impedance











3 Package Specifications

This section shows the package specifications for the MSCDC200H70AG device.

3.1 Package Outline Drawing

The following drawing shows the package outline of the MSCDC200H70AG device. The dimensions in the following figure are in millimeters.

Figure 4 • Package Outline Drawing

